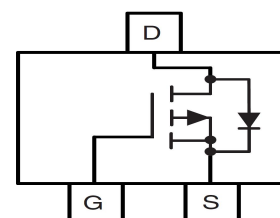
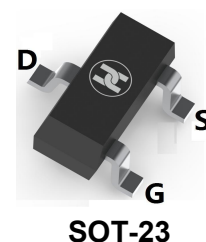


P-Channel Power MOSFET
FEATURES

- Generation V Technology
- Ultra Low On-Resistance
- Low Profile (<1.1mm)
- Fast Switching

MECHANICAL DATA

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)


MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

	Parameter	Max.	Units
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ -10V	-0.76	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ -10V	-0.61	
I _{DM}	Pulsed Drain Current ①	-4.8	
P _D @ T _A = 25°C	Power Dissipation	540	mW
	Linear Derating Factor	4.3	mW/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	-5.0	V/ns
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C
R _{θJA}	Maximum Junction-to-Ambient ④	230	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.029	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(ON)}	Static Drain-to-Source On-Resistance	—	—	0.60	Ω	V _{GS} = -10V, I _D = -0.60A ③
		—	—	1.0		V _{GS} = -4.5V, I _D = -0.30A ③
V _{GS(th)}	Gate Threshold Voltage	-1.0	—	—	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	0.44	—	—	S	V _{DS} = -10V, I _D = -0.30A
I _{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V _{DS} = -24V, V _{GS} = 0V
		—	—	-25		V _{DS} = -24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 20V
Q _g	Total Gate Charge	—	3.4	5.1	nC	I _D = -0.60A
Q _{gs}	Gate-to-Source Charge	—	0.52	0.78		V _{DS} = -24V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	1.1	1.7		V _{GS} = -10V, See Fig. 6 and 9 ③
t _{d(on)}	Turn-On Delay Time	—	10	—	ns	V _{DD} = -15V
t _r	Rise Time	—	8.2	—		I _D = -0.60A
t _{d(off)}	Turn-Off Delay Time	—	23	—		R _G = 6.2Ω
t _f	Fall Time	—	16	—		R _D = 25Ω, See Fig. 10 ③
C _{iss}	Input Capacitance	—	75	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	37	—		V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance	—	18	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-0.54	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-4.8		
V _{SD}	Diode Forward Voltage	—	—	-1.2	V	T _J = 25°C, I _S = -0.60A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	26	39	ns	T _J = 25°C, I _F = -0.60A
Q _{rr}	Reverse Recovery Charge	—	20	30	nC	di/dt = 100A/μs ③

Notes: ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② I_{SD} ≤ -0.60A, di/dt ≤ 110A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C

③ Pulse width ≤ 300 μs; duty cycle ≤ 2%.

④ Surface mounted on FR-4 board, t ≤ 5sec.

P-Channel Power MOSFET

Typical Characteristics

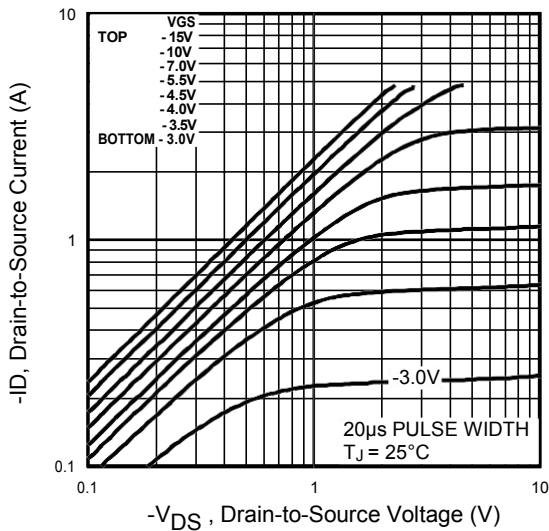


Fig 1. Typical Output Characteristics

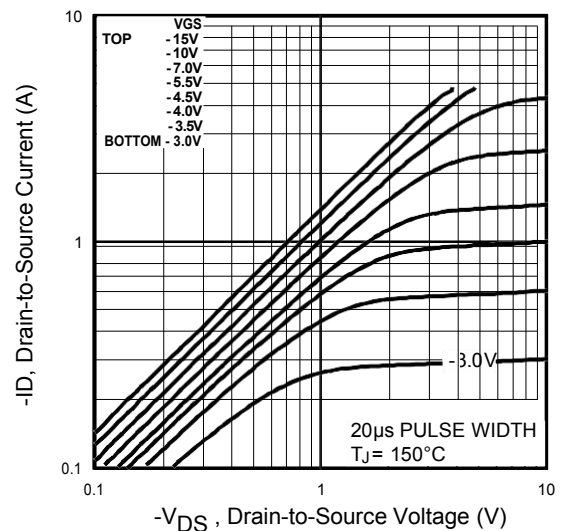


Fig 2. Typical Output Characteristics

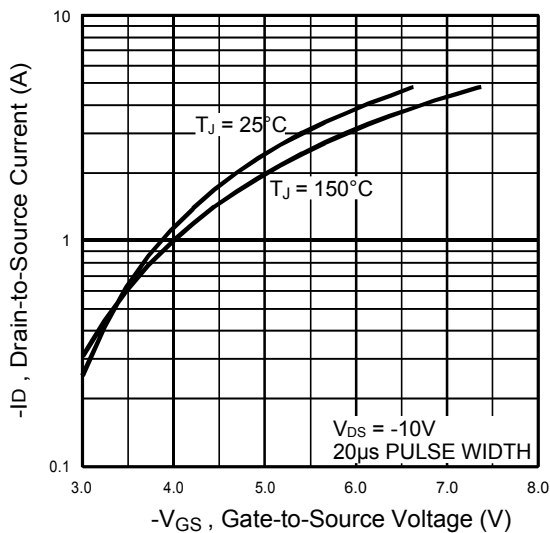


Fig 3. Typical Transfer Characteristics

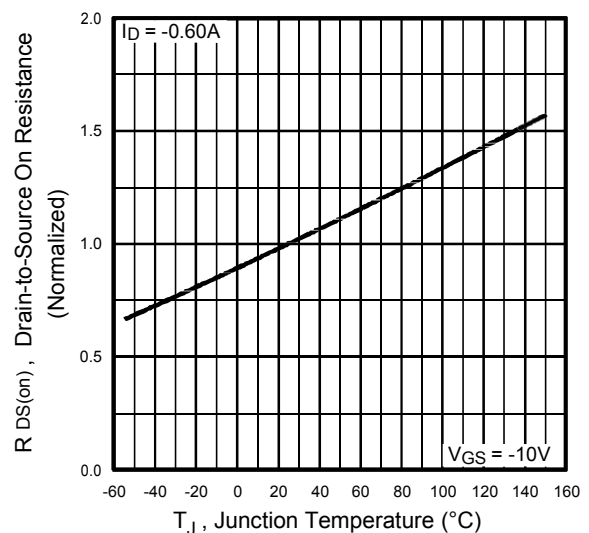


Fig 4. Normalized On-Resistance Vs. Temperature

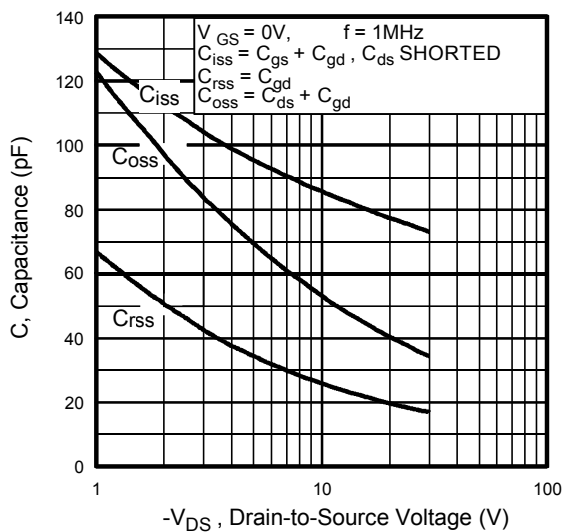


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

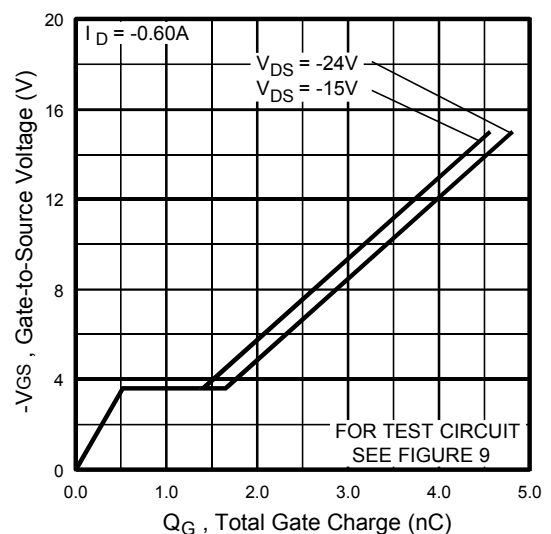


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

P-Channel Power MOSFET

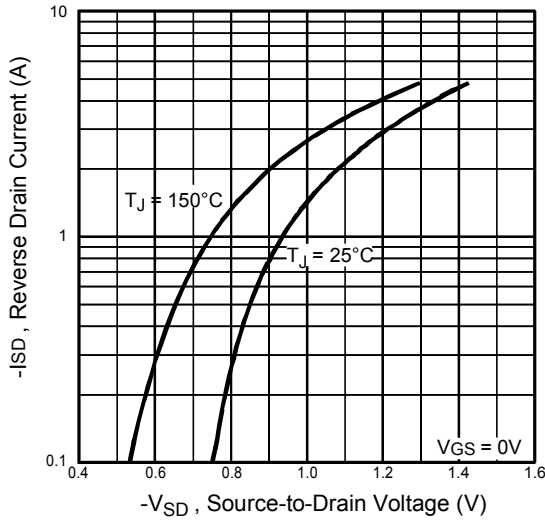


Fig 7. Typical Source-Drain Diode Forward Voltage

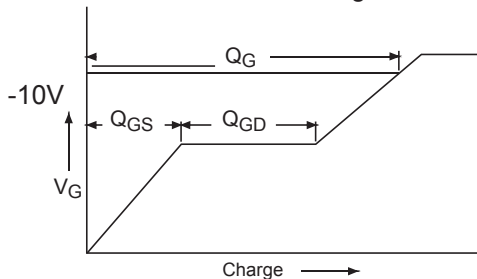


Fig 9a. Basic Gate Charge Waveform

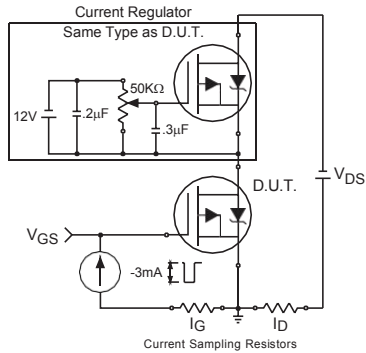


Fig 9b. Gate Charge Test Circuit

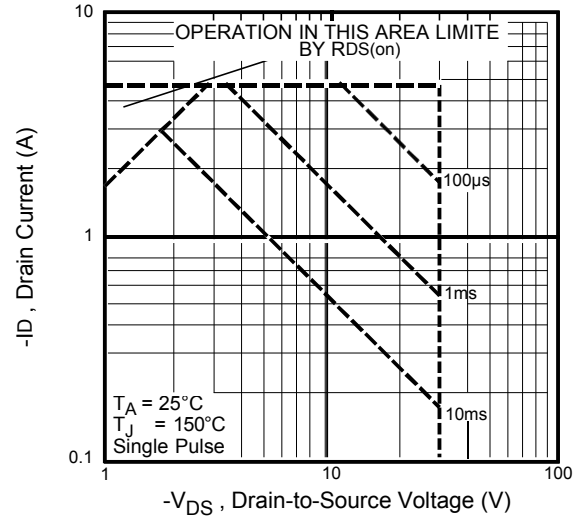


Fig 8. Maximum Safe Operating Area

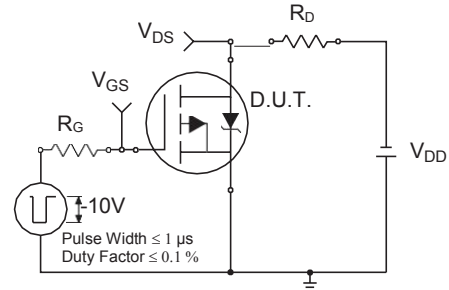


Fig 10a. Switching Time Test Circuit

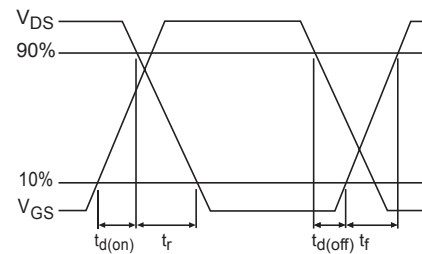


Fig 10b. Switching Time Waveforms

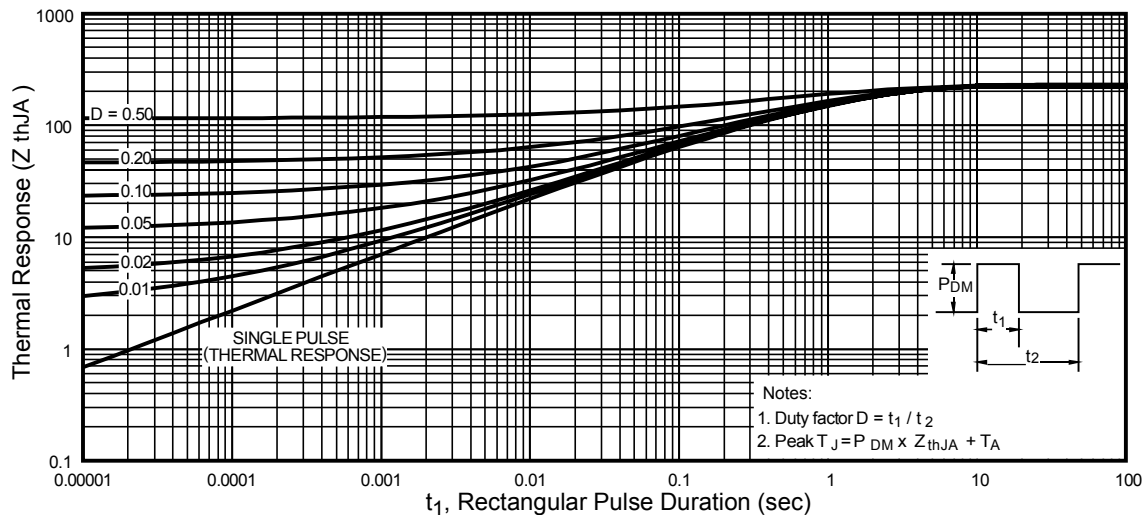
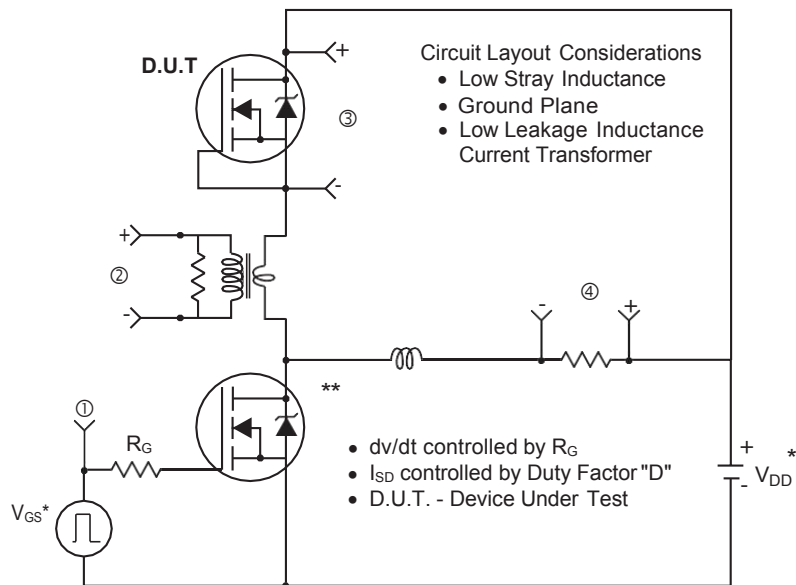


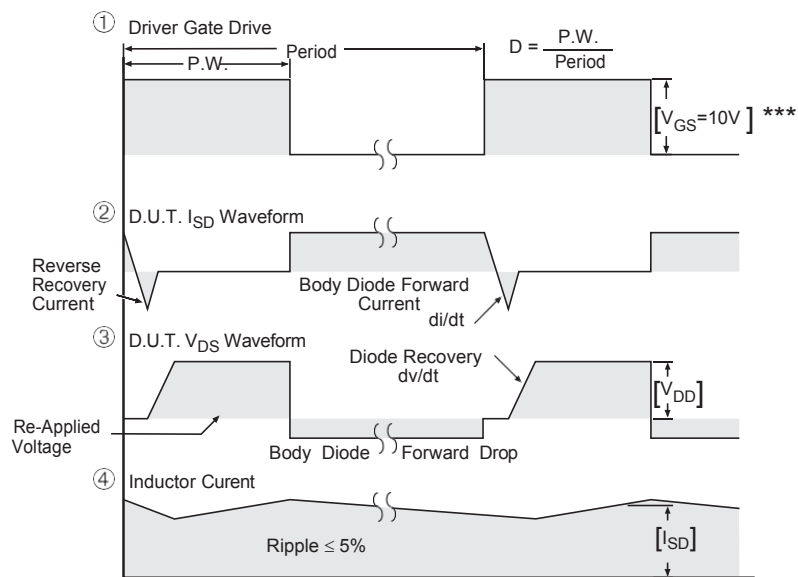
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Peak Diode Recovery dv/dt Test Circuit



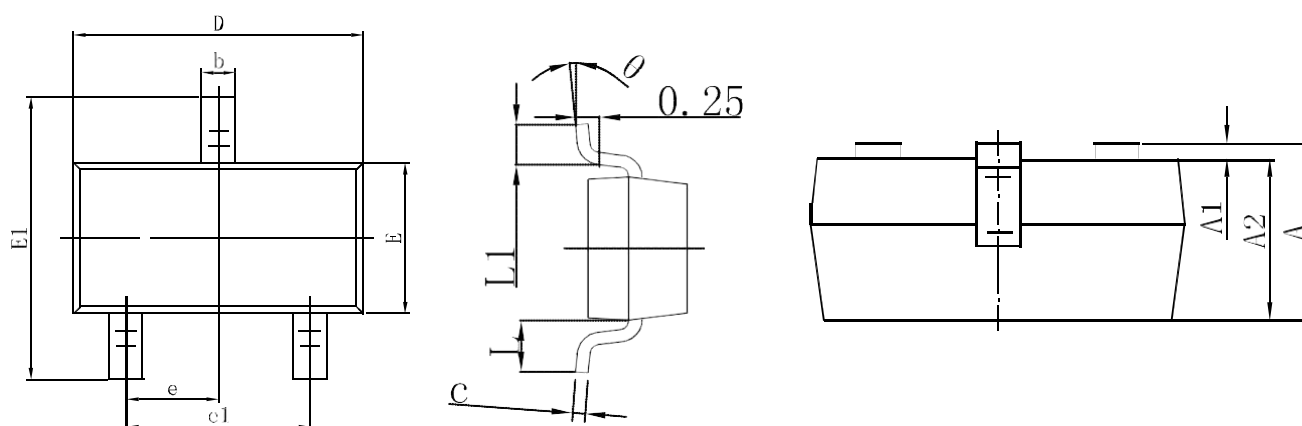
* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements

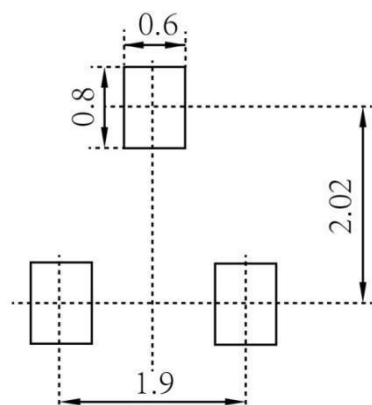


*** $V_{GS} = 5.0V$ for Logic Level and GV Drive Devices

Fig 13. For P-Channel HEXFETS

P-Channel Power MOSFET
SOT-23 Package Outline Dimensions


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

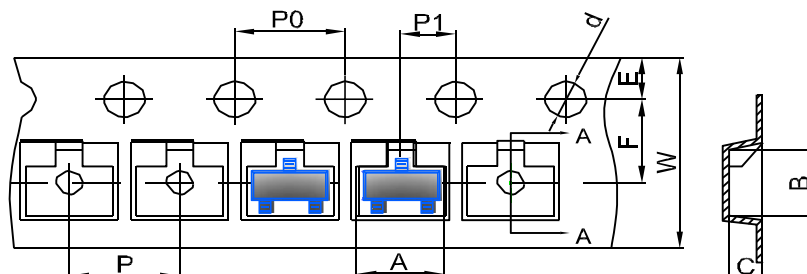
SOT-23 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

P-Channel Power MOSFET

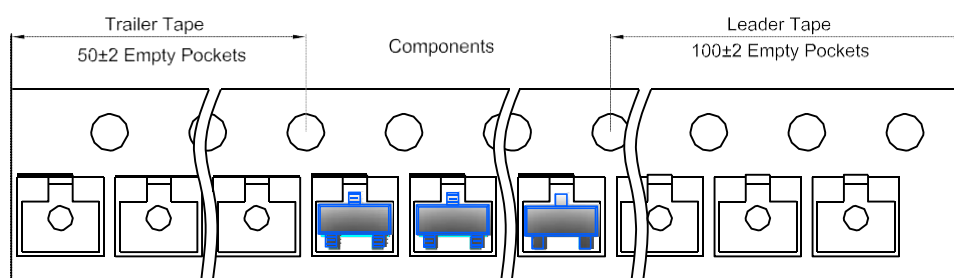
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

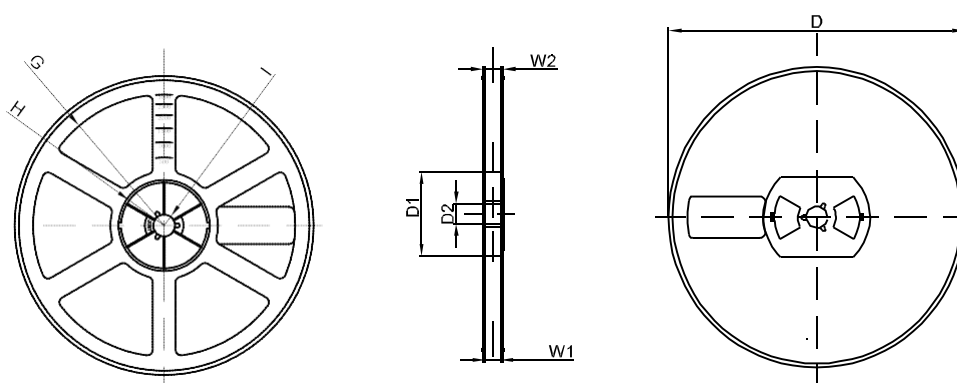


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer



SOT-23 Reel



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1